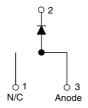


### Vishay High Power Products

# HEXFRED® Ultrafast Soft Recovery Diode, 16 A





D<sup>2</sup>PAK

PRODUCT SUMMARY				
$V_{R}$	1200 V			
V <sub>F</sub> at 16 A at 25 °C	3 V			
I <sub>F(AV)</sub>	16 A			
t <sub>rr</sub> (typical)	30 ns			
T <sub>J</sub> (maximum)	150 °C			
Q <sub>rr</sub> (typical)	260 nC			
dI <sub>(rec)M</sub> /dt (typical) at 125 °C	76 A/μs			
IppM (typical)	5.8 A			

#### **FEATURES**

- Ultrafast recovery
- · Ultrasoft recovery
- Very low I<sub>RRM</sub>
- Very low Q<sub>rr</sub>
- · Specified at operating conditions
- · Designed and qualified for industrial level

#### **BENEFITS**

- · Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

#### **DESCRIPTION**

HFA16TB120S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 16 A continuous current, the HFA16TB120S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>RRM</sub>) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA16TB120S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode voltage	$V_{R}$		1200	V	
Maximum continuous forward current	l <sub>F</sub>	T <sub>C</sub> = 100 °C	16		
Single pulse forward current	I <sub>FSM</sub>		190	Α	
Maximum repetitive forward current	I <sub>FRM</sub>		64		
Maximum power dissipation	$P_{D}$	T <sub>C</sub> = 25 °C	151	w	
		T <sub>C</sub> = 100 °C	60	VV	
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 55 to + 150	°C	

Document Number: 93075 Revision: 22-Oct-08

### **HFA16TB120S**

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<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V <sub>BR</sub>	Ι <sub>R</sub> = 100 μΑ		1200	-	-	
	I <sub>F</sub> = 16 A		-	2.5	3.0	V	
Maximum forward voltage V <sub>FM</sub>	$V_{FM}$	I <sub>F</sub> = 32 A	See fig. 1	-	3.2	3.93	
		I <sub>F</sub> = 16 A, T <sub>J</sub> = 125 °C	-		2.3	2.7	
Maximum reverse	_	$V_R = V_R$ rated	Soo fig. 0	-	0.75	20	- μΑ
leakage current	I <sub>RM</sub>	T <sub>J</sub> = 125 °C, V <sub>R</sub> = 0.8 x V <sub>R</sub> rated	See fig. 2	-	375	2000	
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	See fig. 3	-	27	40	pF
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body - 8.0		8.0	-	nH	

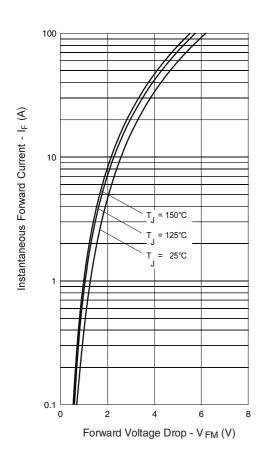
<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	30	-	
Reverse recovery time See fig. 5 and 10	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	90	135	ns
occ lig. 5 and 10	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	164	245	
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	5.8	10	Α
See fig. 6	$I_{RRM2}$ $I_{J} = 125 ^{\circ}\text{C}$ $I_{F} = 16 ^{\circ}\text{A}$	-	8.3	15	"		
Reverse recovery charge	Q <sub>rr1</sub>	$T_J = 25 ^{\circ}\text{C}$ $dI_F/dt = 200 \text{A/}\mu\text{s}$	-	260	675	nC	
See fig. 7	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C	V <sub>R</sub> = 200 V	-	680	1838	
Peak rate of fall of recovery current during t <sub>b</sub> See fig. 8	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	120	-	- A/μs
	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	76	-	Αίμο

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	0.83	K/W
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	80	N/VV
Weight			-	2.0	-	g
Weight		-	0.07	1	oz.	
Marking device		Case style D <sup>2</sup> PAK		HFA16	TB120S	-

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## HEXFRED® Vishay High Power Products Ultrafast Soft Recovery Diode, 16 A



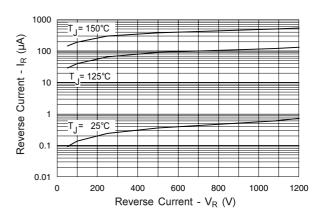


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

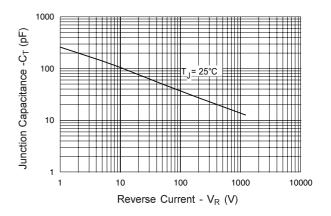


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

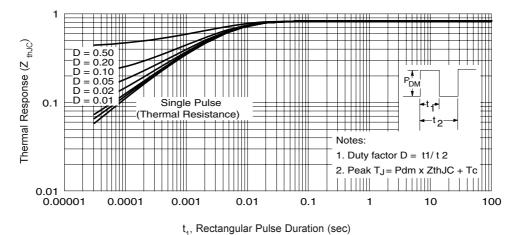


Fig. 4 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics

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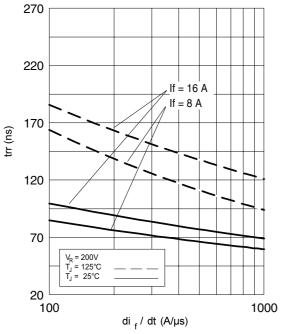


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt (Per Leg)

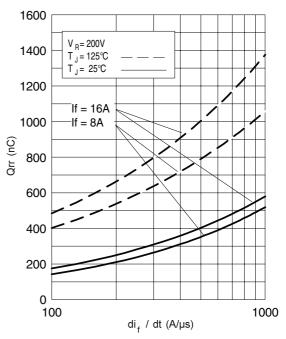


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt (Per Leg)

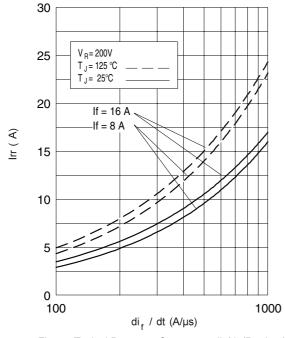


Fig. 6 - Typical Recovery Current vs.  $di_{\text{F}}/dt$  (Per Leg)

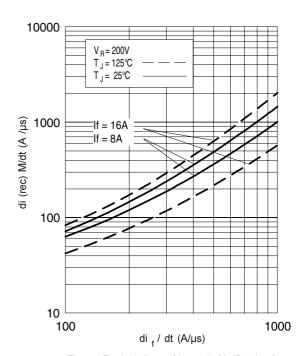


Fig. 8 - Typical  $dI_{(rec)M}/dt$  vs.  $dI_F/dt$  (Per Leg)



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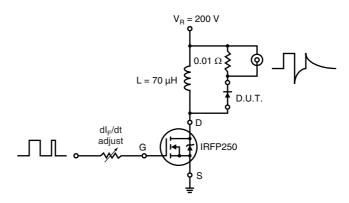
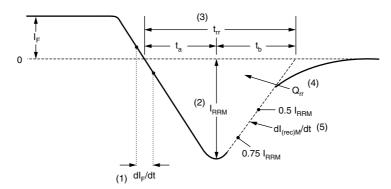


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 10 - Reverse Recovery Waveform and Definitions

LINKS TO RELATED DOCUMENTS				
Dimensions http://www.vishay.com/doc?95046				
Part marking information http://www.vishay.com/doc?95054				
Packaging information	http://www.vishay.com/doc?95032			





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Document Number: 91000 Revision: 18-Jul-08

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